

ABSTRACT

The present invention is an ablation processing method for forming a processed recessed portion on a surface of a substrate through ablation processing using irradiation energy of a laser beam, and the ablation processing is performed such that an angle formed by a sidewall surface of the processed recessed portion on an opening side of the processed recessed portion and the surface of the substrate is 80° or more and 90° or less. Accordingly, a substrate for use in a semiconductor package substrate that enables densification and reduction in wiring resistance and exhibits high performance can be provided.